



SUPER-SEMI



SUPER-MOSFET

Super Junction Metal Oxide Semiconductor Field Effect Transistor

900V Super Junction Power MOSFET Gen-II
SS*90R160S2

Rev. 1.2
Dec. 2022

www.supersemi.com.cn

SSW90R160S2

900V N-Channel Super-Junction MOSFET Gen-II

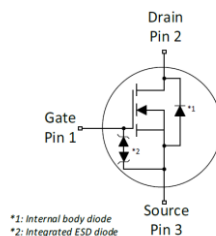
Description

SJ-FET is new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance. This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. SJ-FET is suitable for various AC/DC power conversion in switching mode operation for higher efficiency.

Features

- Multi-Epi process SJ-FET
- 950V @T_J = 150 °C
- Typ. R_{DS(on)} = 0.138Ω
- Ultra Low Gate Charge (typ. Q_g = 57.5nC)
- 100% avalanche tested
- Integrated Zener diode for high ESD robustness(>2kV HBM)

SSW90R160S2



Absolute Maximum Ratings

Symbol	Parameter	SSW90R160S2	Unit
V _{DSS}	Drain-Source Voltage	900	V
I _D	Drain Current -Continuous (TC = 25°C) -Continuous (TC = 100°C)	25* 15.8*	A
I _{DM}	Drain Current - Pulsed (Note 1)	75	A
V _{GSS}	Gate-Source voltage	±30	V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	960	mJ
I _{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _J max)	8	A
dv/dt	Peak Diode Recovery dv/dt (Note 3)	15	V/ns
dV _{DS} /dt	Drain Source voltage slope (V _{DS} =480V)	50	V/ns
P _D	Power Dissipation (TC = 25°C)	190	W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering Purpose, 1/16" from Case for 10 Seconds	260	°C

* Drain current limited by maximum junction temperature. Maximum duty cycle D=0.75

Thermal Characteristics

Symbol	Parameter	SSW90R160S2	Unit
R _{θJC}	Thermal Resistance, Junction-to-Case	0.65	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink Typ.	0.5	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	62	°C/W



Electrical Characteristics TC = 25°C unless otherwise noted

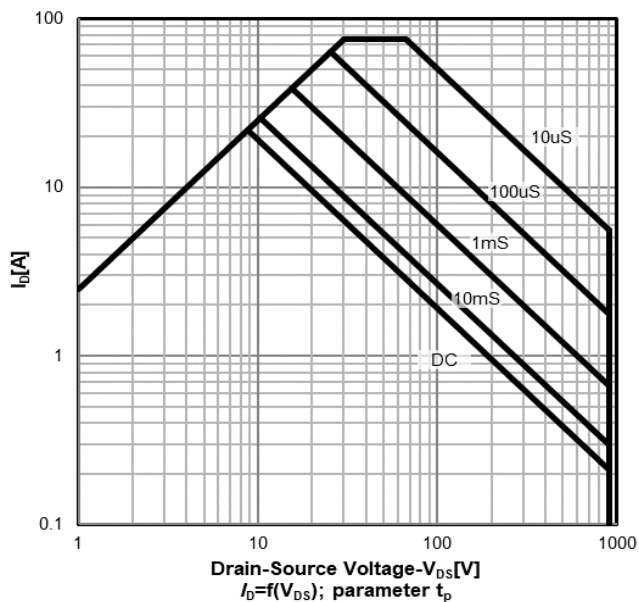
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA, T _J = 25°C	900	-	-	V
		V _{GS} = 0V, I _D = 250μA, T _J = 150°C	950	-	-	V
ΔBV _{DSS} /ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.8	-	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 900V, V _{GS} = 0V -T _J = 125°C	-	-	1 100	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20V, V _{DS} = 0V	-	-	1	μA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20V, V _{DS} = 0V	-	-	-1	μA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3.0	4.0	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 12A	-	0.138	0.16	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 50V, V _{GS} = 0V, f = 1.0MHz	-	2850	-	pF
C _{oss}	Output Capacitance		-	90	-	pF
C _{rss}	Reverse Transfer Capacitance		-	2.4	-	pF
E _{oss}	Stored Energy in Output Capacitance	V _{DS} = 0 to 600V, V _{GS} = 0V	-	10.9	-	μJ
Co(er)	Energy Related Output Capacitance		-	61	-	pF
Co(tr)	Time Related Output Capacitance		-	240	-	pF
Q _g	Total Gate Charge		-	57.5	-	nC
Q _{gs}	Gate-Source Charge	V _{DS} = 400V, I _D = 12A, V _{GS} = 10V (Note 4)	-	15.8	-	nC
Q _{gd}	Gate-Drain Charge		-	19.5	-	nC
V _{plateau}	Gate plateau voltage		-	5.6	-	V
R _g	Gate resistance	f=1 MHz, open drain	-	4.5	-	Ω
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} = 400V, I _D = 12A R _G = 4.7Ω, V _{GS} = 10V (Note 4)	-	27	-	ns
t _r	Turn-On Rise Time		-	18	-	ns
t _{d(off)}	Turn-Off Delay Time		-	89	-	ns
t _f	Turn-Off Fall Time		-	15	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		-	-	25	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		-	-	75	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 25A	-	0.9	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, V _{DS} = 400V, I _S = 12A, dI _F /dt =100A/μs	-	400	-	ns
Q _{rr}	Reverse Recovery Charge		-	6.4	-	μC
I _{rrm}	Peak Reverse Recovery Current		-	30	-	A

NOTES:

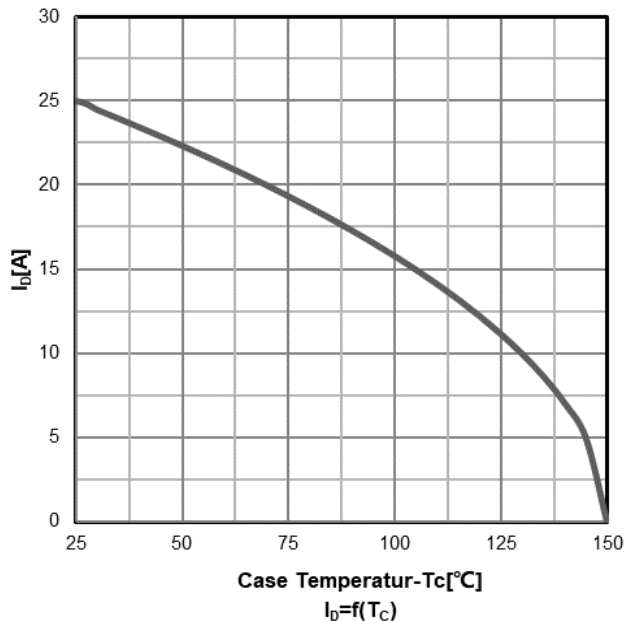
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_D=I_{AS}, V_{DD}=100V, L=30mH, Starting T_J=25 °C
3. I_{SD}≤I_D, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25 °C
4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

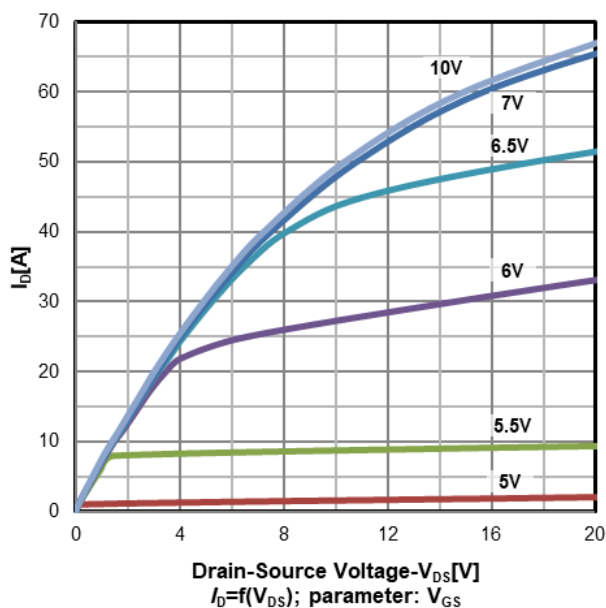
Safe operating area TC=25 °C
Non FullPAK



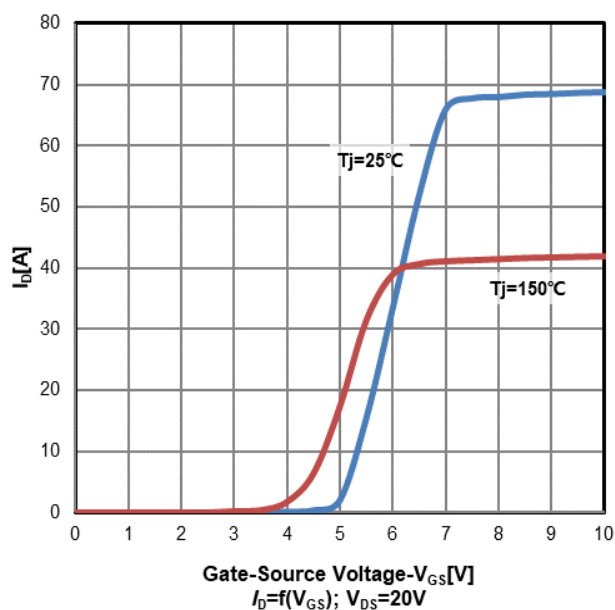
Drain current vs temperature



Typ. output characteristics $T_J=25\text{ }^{\circ}\text{C}$

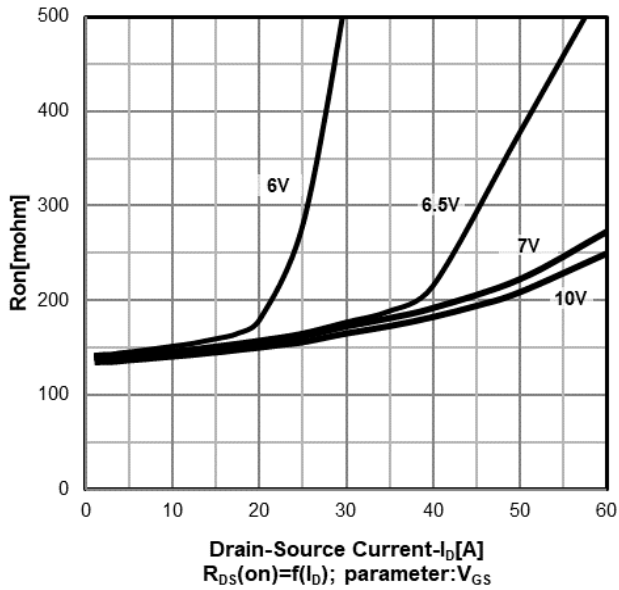


Typ. transfer characteristics

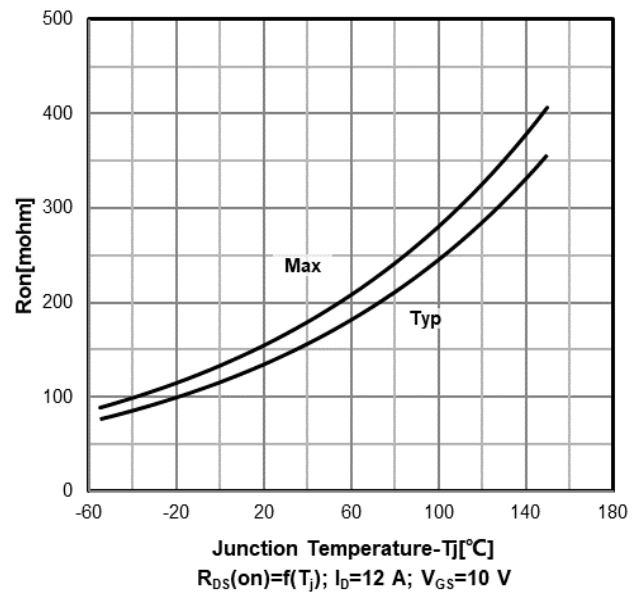


Typical Performance Characteristics

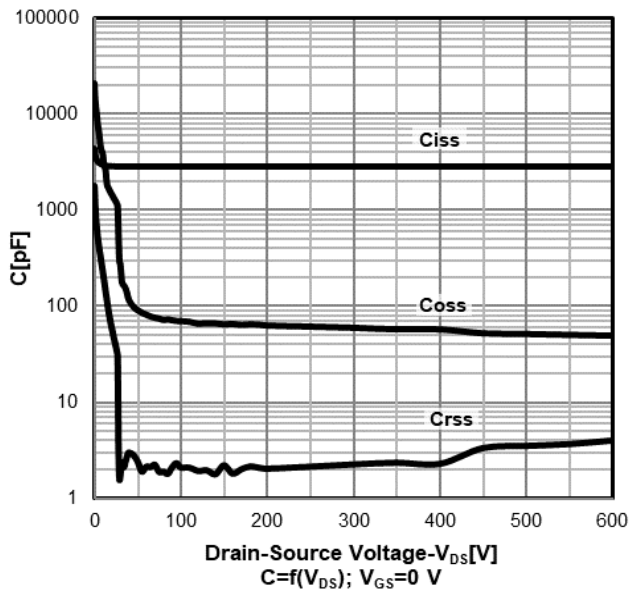
Typ. drain-source on-state resistance



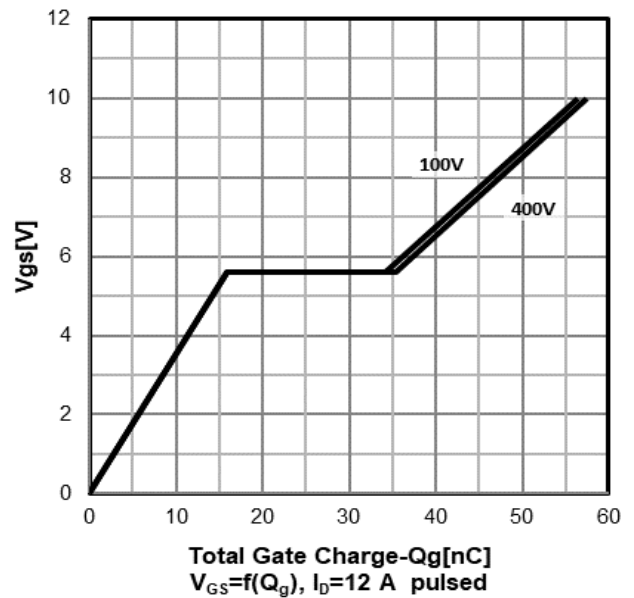
On resistance vs temperature



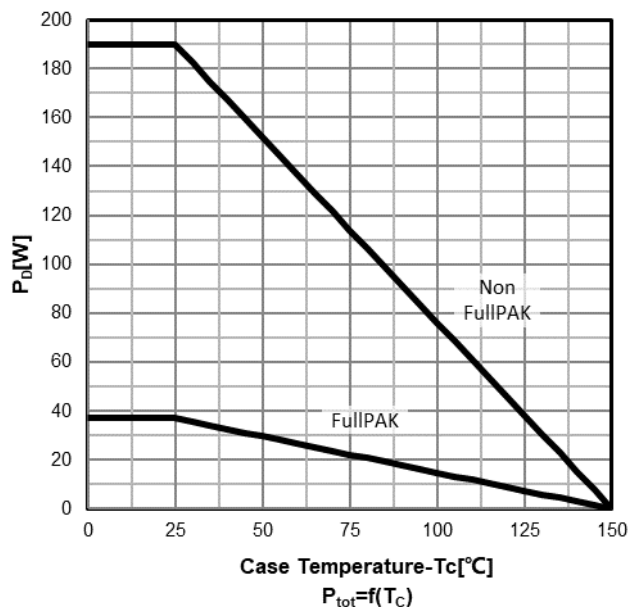
Typ. capacitances



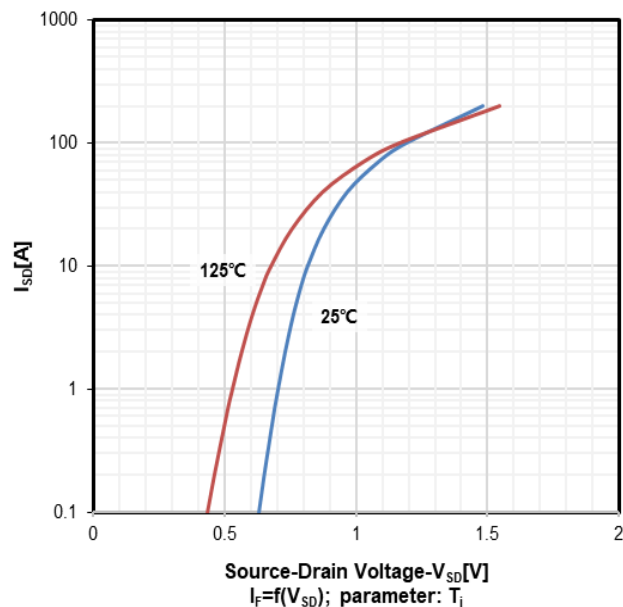
Typ. gate charge characteristics



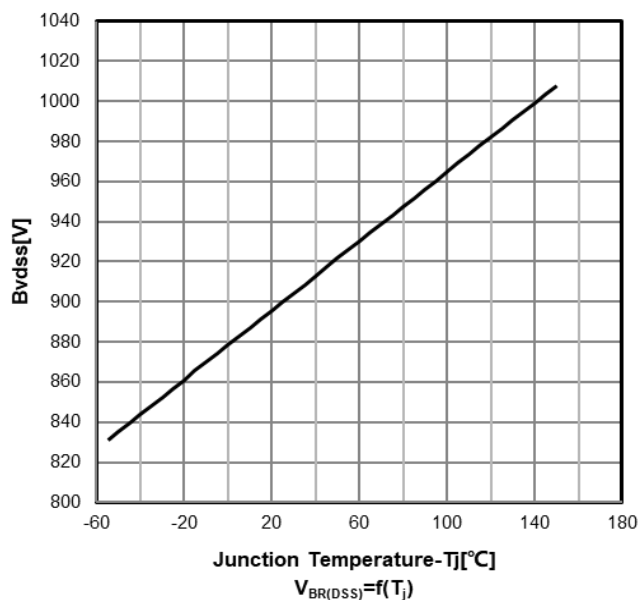
Power dissipation



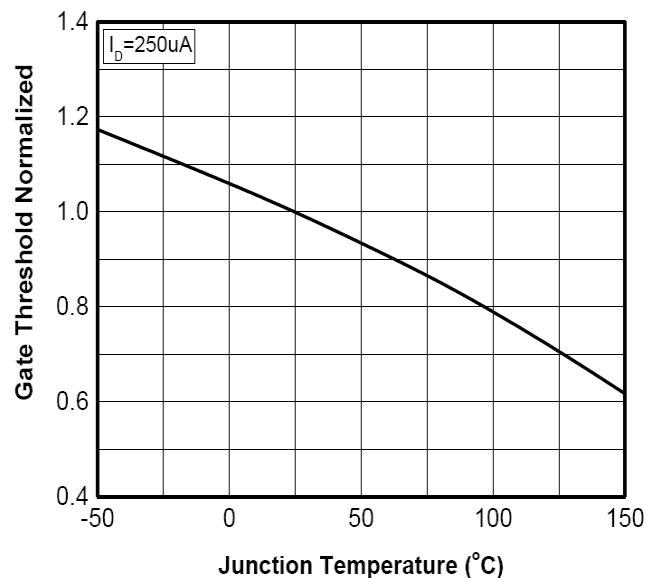
Forward characteristics of reverse diode



Drain-source breakdown voltage



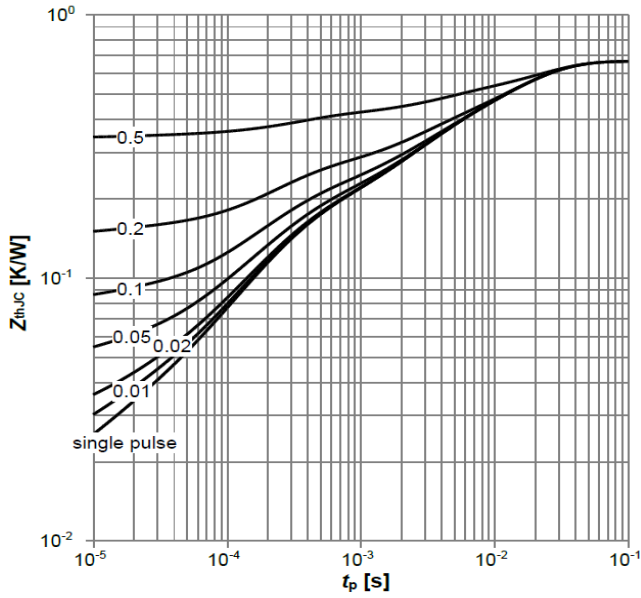
Normalized $V_{GS(th)}$ characteristics



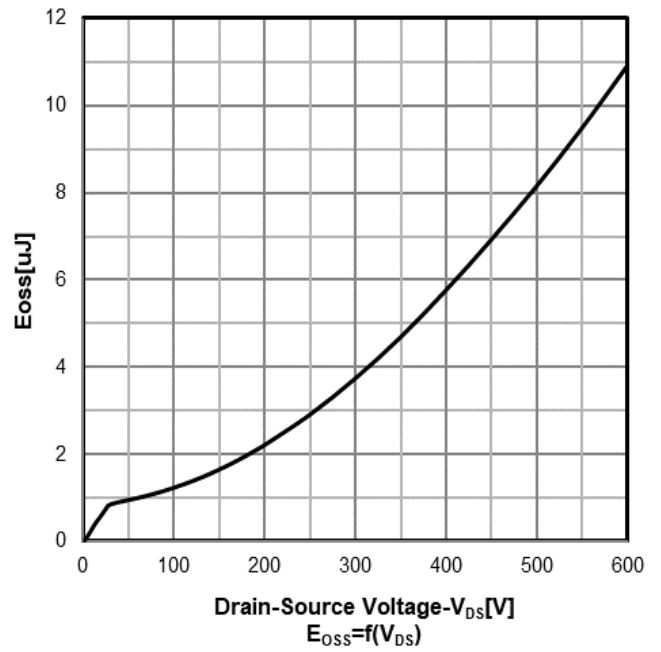


Typical Performance Characteristics

Max. transient thermal impedance
parameter: $D=tp/T$; Non-FullPAK

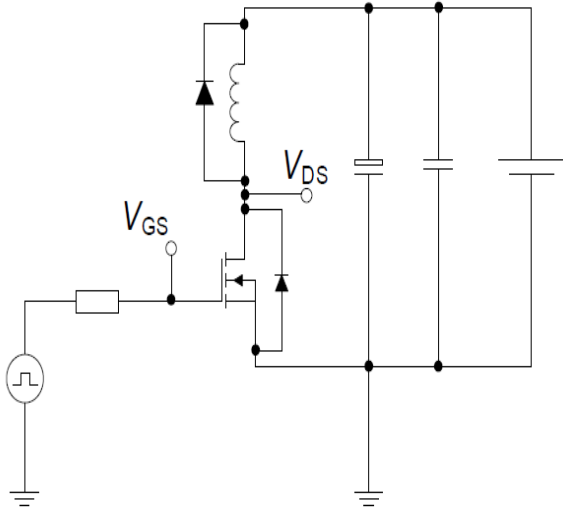


Coss stored energy

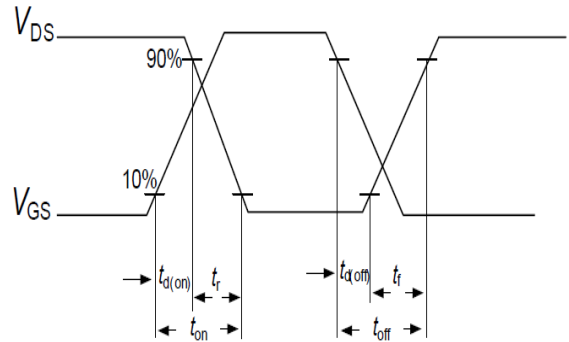


Switching times test circuit and waveform for inductive load

Switching times test circuit for inductive load

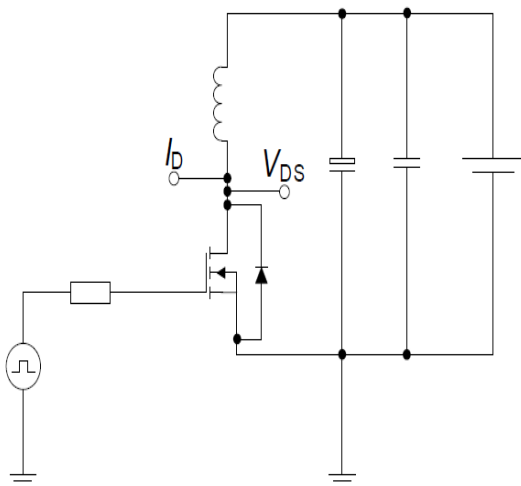


Switching time waveform

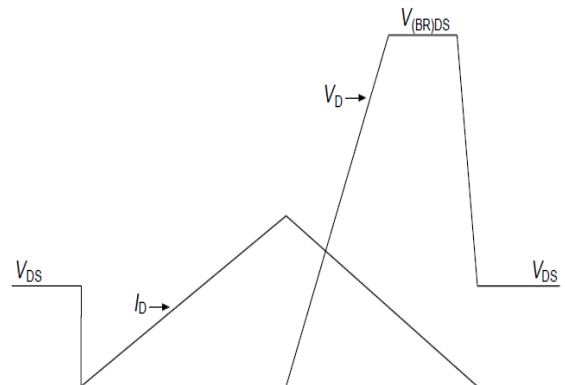


Unclamped inductive load test circuit and waveform

Unclamped inductive load test circuit

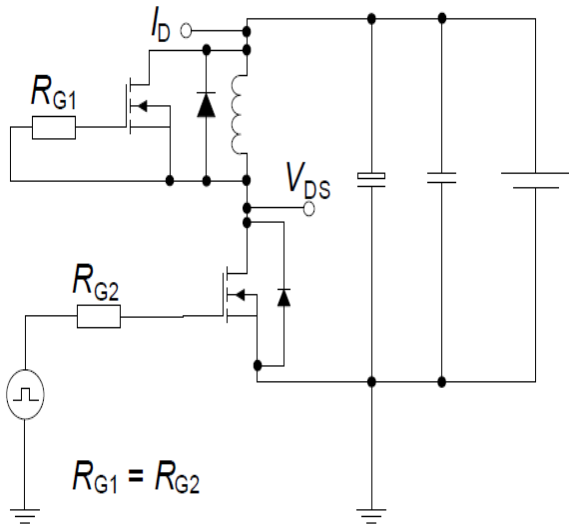


Unclamped inductive waveform

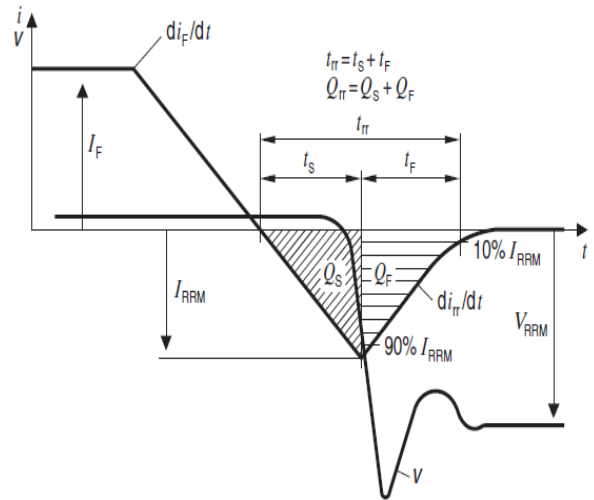


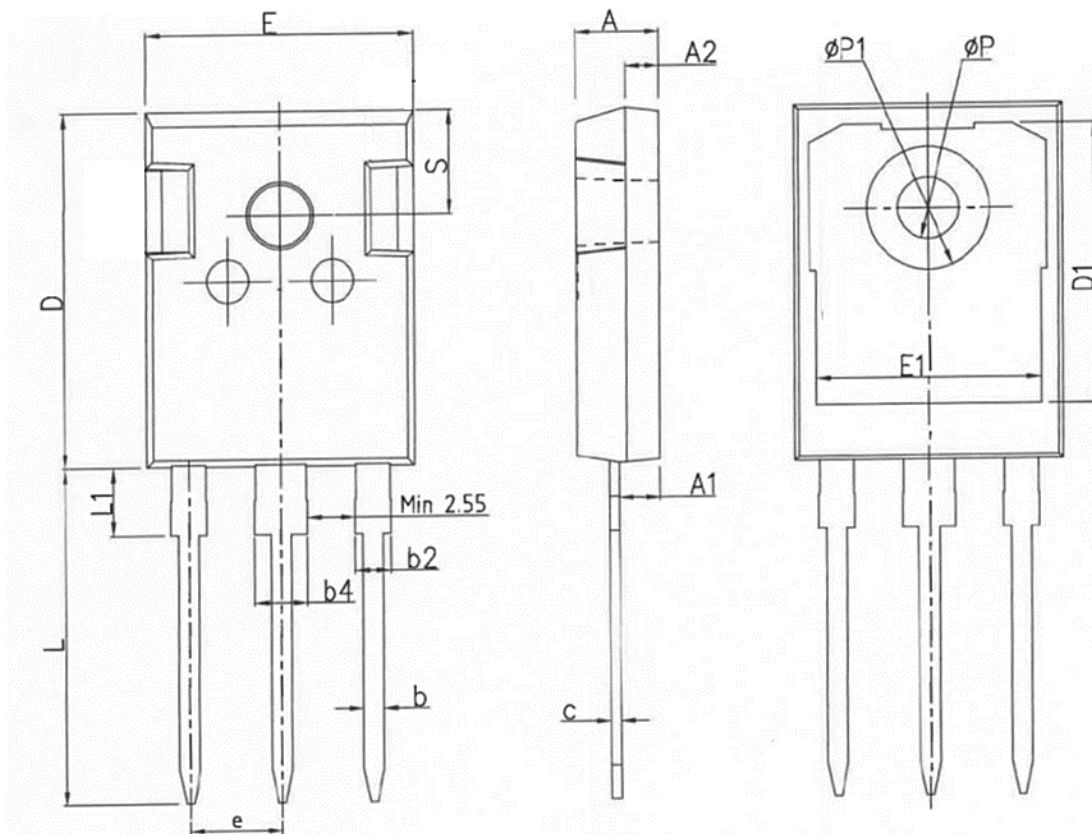
Test circuit and waveform for diode characteristics

Test circuit for diode characteristics



Diode recovery waveform





COMMON DIMENSIONS

SYMBOL	UNIT(mm)		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.20	2.40	2.60
A2	1.85	2.00	2.15
b	1.10	1.20	1.35
b2	1.91	2.04	2.21
b4	2.91	3.04	3.21
c	0.50	0.60	0.75
D	20.70	21.00	21.30
D1	16.20	16.55	16.90
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
e	5.44BSC		
L	19.60	19.95	20.30
L1	-	-	4.30
ΦP	3.40	3.60	3.80
ΦP1	-	-	7.50
S	6.15BSC		



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